



PHE13005

Silicon diffused power transistor

21 January 2014

Product data sheet

1. General description

High voltage, high speed NPN planar-passivated power switching transistor in a SOT78 plastic package intended for use in high frequency electronic lighting ballast applications

2. Features and benefits

- Fast switching
- High voltage capability of 700 V
- Low thermal resistance

3. Applications

- Electronic lighting ballasts

4. Quick reference data

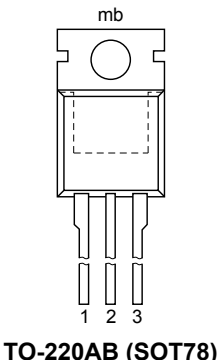
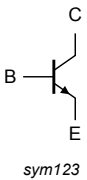
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	DC; Fig. 4 ; Fig. 1 ; Fig. 2	-	-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; Fig. 3	-	-	75	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	700	V
Static characteristics						
h_{FE}	DC current gain	$I_C = 1\text{ A}$; $V_{CE} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 11	12	20	40	
		$I_C = 2\text{ A}$; $V_{CE} = 5\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 11	10	17	28	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	C	collector		
3	E	emitter		
mb	C	mounting base; connected to collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHE13005	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	collector-base voltage	$I_E = 0\text{ A}$	-	700	V
V_{CEO}	collector-emitter voltage	$I_B = 0\text{ A}$	-	400	V
I_C	collector current	DC; Fig. 4 ; Fig. 1 ; Fig. 2	-	4	A
I_{CM}	peak collector current		-	8	A
I_B	base current	DC	-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; Fig. 3	-	75	W
T_{stg}	storage temperature		-65	150	°C
T_j	junction temperature		-	150	°C
V_{EBO}	emitter-base voltage	$I_C = 0\text{ A}$	-	9	V

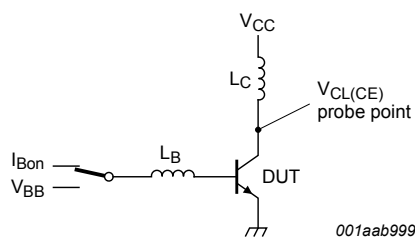


Fig. 1. Test circuit for reverse bias safe operating area

$$V_{CL(CE)} \leq 1000 \text{ V}; V_{CC} = 150 \text{ V}; V_{BB} = -5 \text{ V};$$

$$L_B = 1 \mu\text{H}; L_C = 200 \mu\text{H}$$

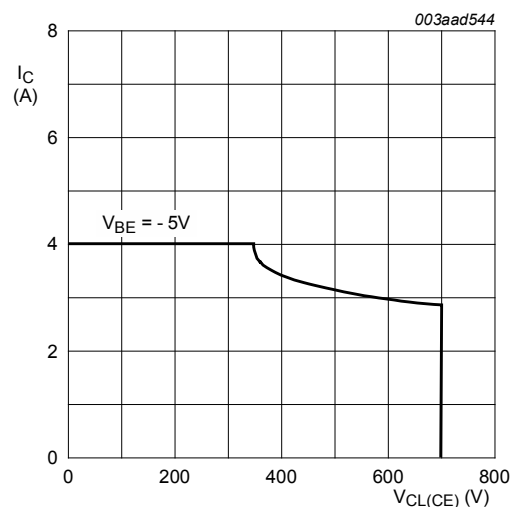


Fig. 2. Reverse bias safe operating area

$$T_j \leq T_{j(\max)} \text{ } ^\circ\text{C}$$

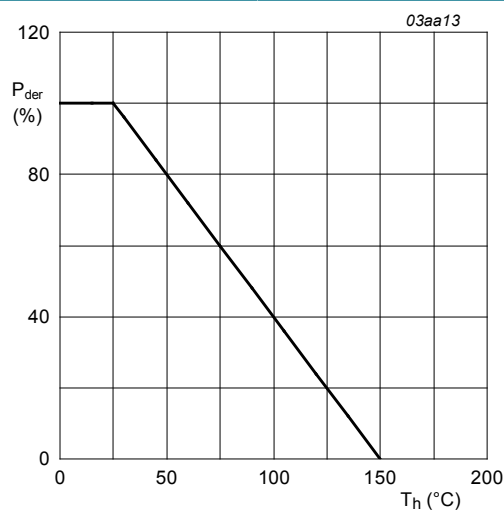


Fig. 3. Normalized total power dissipation as a function of heatsink temperature

$$P_{\text{der}} = \frac{P_{\text{tot}}}{P_{\text{tot}(25^\circ\text{C})}} \times 100 \%$$

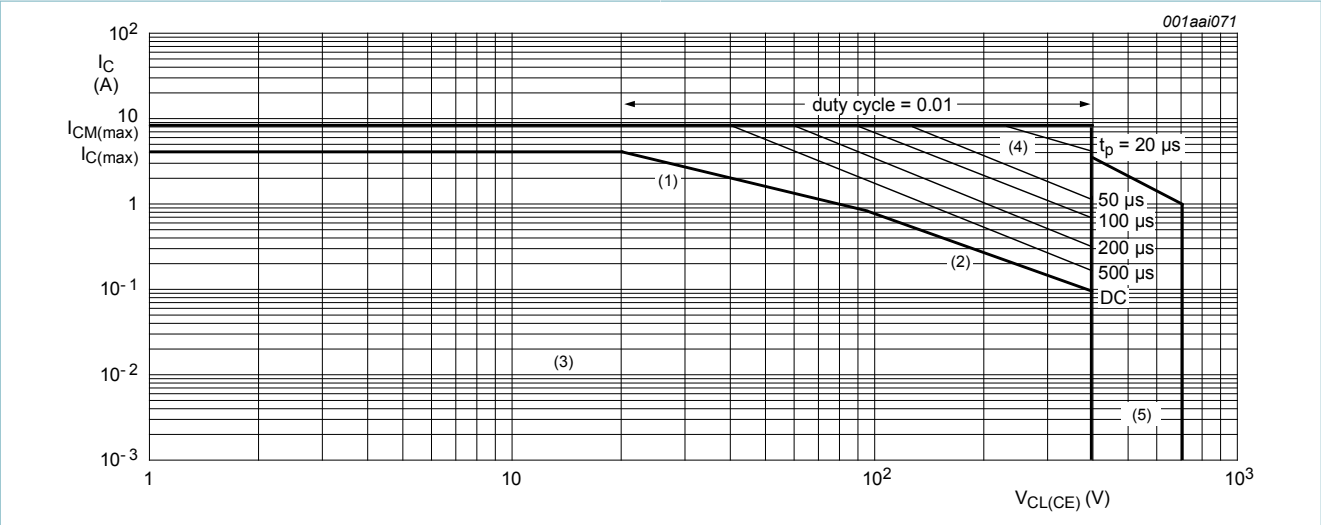


Fig. 4. Forward bias safe operating area

k maximum lines(2)Second breakdown limits(3)Region of permissible DC operation(4)Extension of operating region for repetitive pulse operation

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	1.67	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

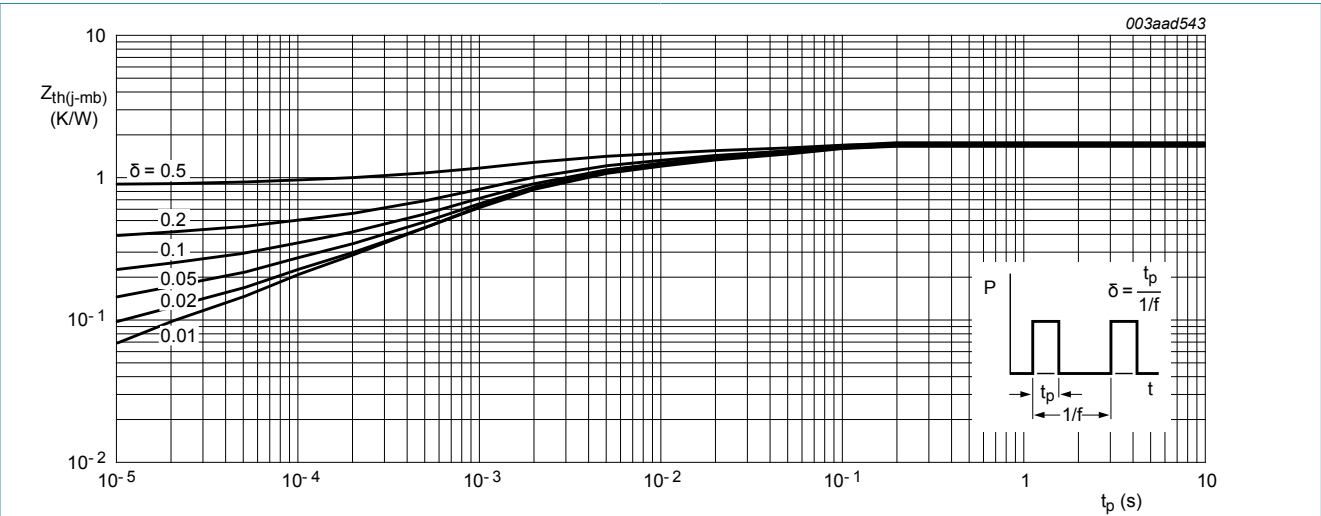


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
t _s	storage time	I _C = 2 A; I _{Bon} = 0.4 A; I _{Boff} = -0.4 A; R _L = 75 Ω; T _{mb} = 25 °C; resistive load; Fig. 12 ; Fig. 13		-	2.7	4	μs
		I _C = 2 A; I _{Bon} = 0.4 A; V _{BB} = -5 V; L _B = 1 μH; T _{mb} = 25 °C; inductive load; Fig. 14 ; Fig. 15		-	1.2	2	μs
		I _C = 2 A; I _{Bon} = 0.4 A; V _{BB} = -5 V; L _B = 1 μH; T _{mb} = 100 °C; inductive load; Fig. 14 ; Fig. 15		-	1.4	4	μs
t _f	fall time	I _C = 2 A; I _{Bon} = 0.4 A; I _{Boff} = -0.4 A; R _L = 75 Ω; T _{mb} = 25 °C; resistive load; Fig. 12 ; Fig. 13		-	0.3	0.9	μs
		I _C = 2 A; I _{Bon} = 0.4 A; V _{BB} = -5 V; L _B = 1 μH; T _{mb} = 25 °C; inductive load; Fig. 14 ; Fig. 15		-	0.1	0.5	μs
		I _C = 2 A; I _{Bon} = 0.4 A; V _{BB} = -5 V; L _B = 1 μH; T _{mb} = 100 °C; inductive load; Fig. 14 ; Fig. 15		-	0.16	0.9	μs
Static characteristics							
I _{CES}	collector-emitter cut-off current	V _{BE} = -1.5 V; V _{CE} = 700 V; T _j = 25 °C		-	-	1	mA
		V _{BE} = -1.5 V; V _{CE} = 700 V; T _j = 100 °C		-	-	5	mA
I _{CBO}	collector-base cut-off current	V _{CB} = 700 V; I _E = 0 A; T _{mb} = 25 °C		-	-	1	mA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 400 V; I _B = 0 A; T _{mb} = 25 °C		-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{mb} = 25 °C		-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage	I _B = 0 A; I _C = 10 mA; L _C = 25 mH; T _{mb} = 25 °C; Fig. 6 ; Fig. 7		400	-	-	V
V _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 0.2 A; T _{mb} = 25 °C; Fig. 8 ; Fig. 9		-	0.1	0.5	V
		I _C = 2 A; I _B = 0.5 A; T _{mb} = 25 °C; Fig. 8 ; Fig. 9		-	0.2	0.6	V
		I _C = 4 A; I _B = 1 A; T _{mb} = 25 °C; Fig. 8 ; Fig. 9		-	0.3	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 0.2 A; T _{mb} = 25 °C; Fig. 10		-	0.85	1.2	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$I_C = 2\text{ A}$; $I_B = 0.5\text{ A}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 10	-	0.92	1.6	V
h_{FE}	DC current gain	$I_C = 1\text{ A}$; $V_{CE} = 5\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 11	12	20	40	
		$I_C = 2\text{ A}$; $V_{CE} = 5\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 11	10	17	28	

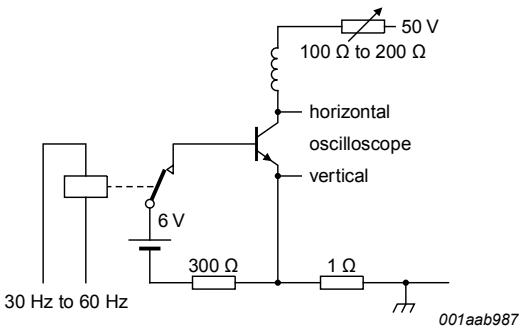


Fig. 6. Test circuit for collector-emitter sustaining voltage

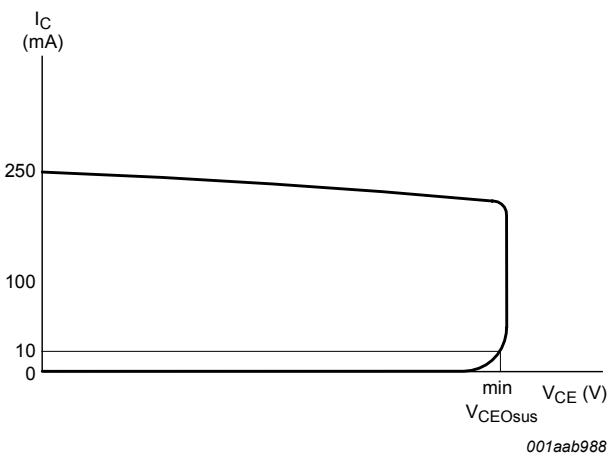


Fig. 7. Oscilloscope display for collector-emitter sustaining voltage test waveform

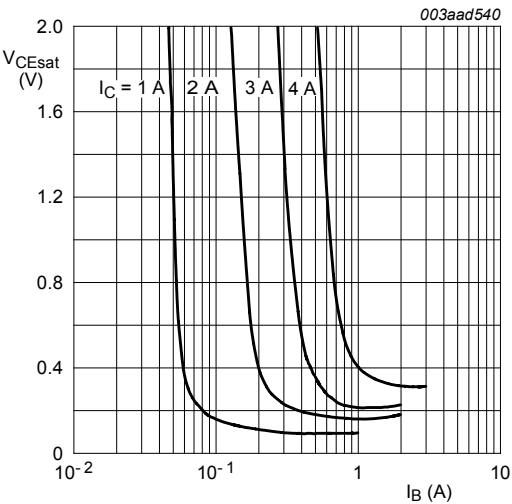


Fig. 8. Collector-emitter saturation voltage; typical values

$T_J = 25\text{ }^\circ\text{C}$

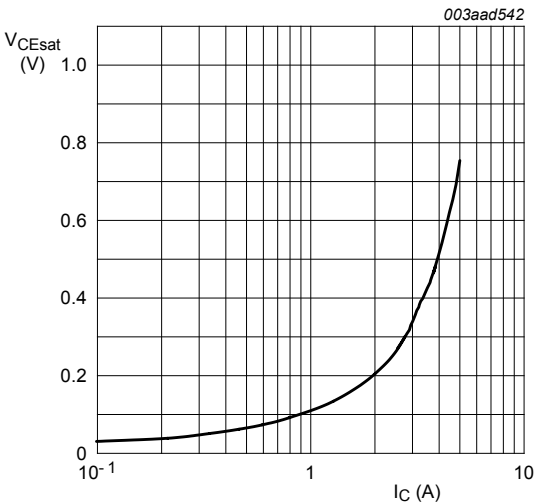


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

$\frac{I_C}{I_B} = 4$

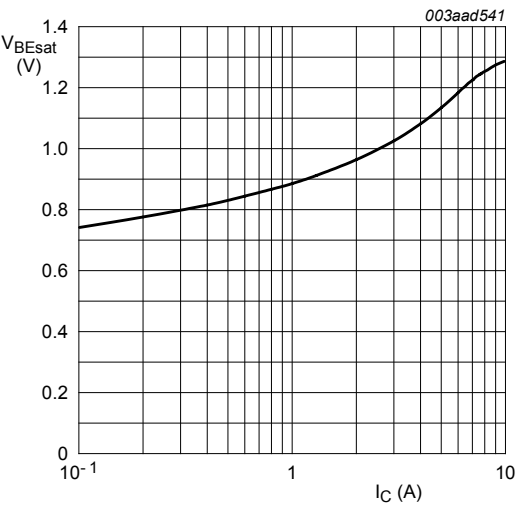


Fig. 10. Base-emitter saturation voltage; typical values

$$\frac{I_C}{I_B} = 4$$

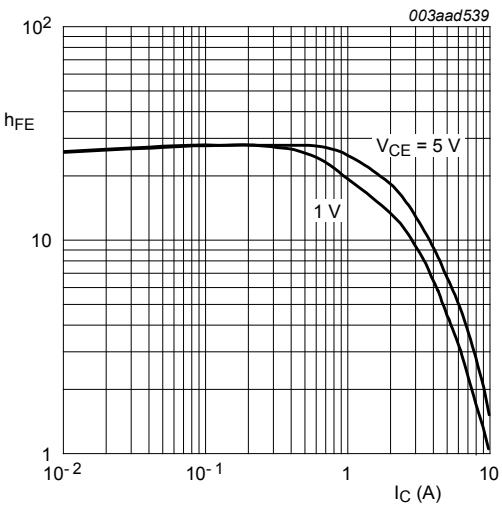


Fig. 11. DC current gain as a function of collector current; typical values

$$T_j = 25\text{ }^{\circ}\text{C}$$

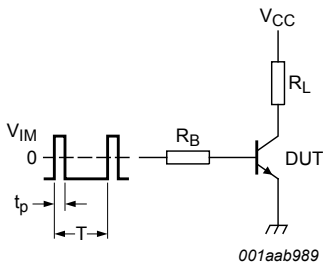


Fig. 12. Test circuit for resistive load switching

$V_{IM} = -6\text{ to }+8\text{ V}$; $V_{CC} = 250\text{ V}$; $t_p = 20\text{ }\mu\text{s}$; $\delta = \frac{t_p}{T} = 0.01$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

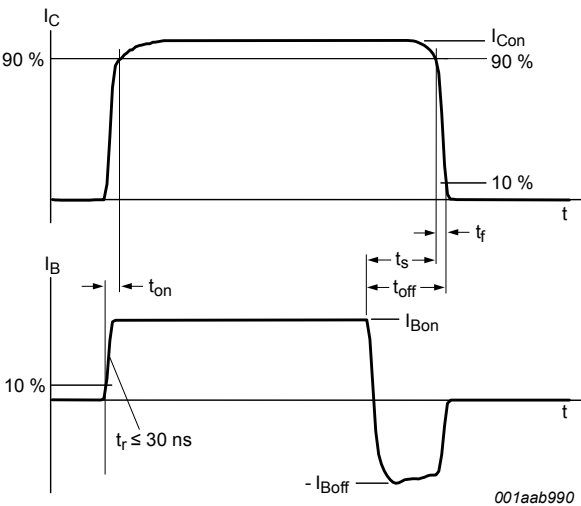


Fig. 13. Switching times waveforms for resistive load

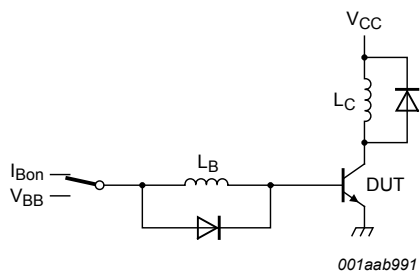


Fig. 14. Test circuit for inductive load switching

$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\text{ }\mu\text{H}; L_B = 1\text{ }\mu\text{H}$

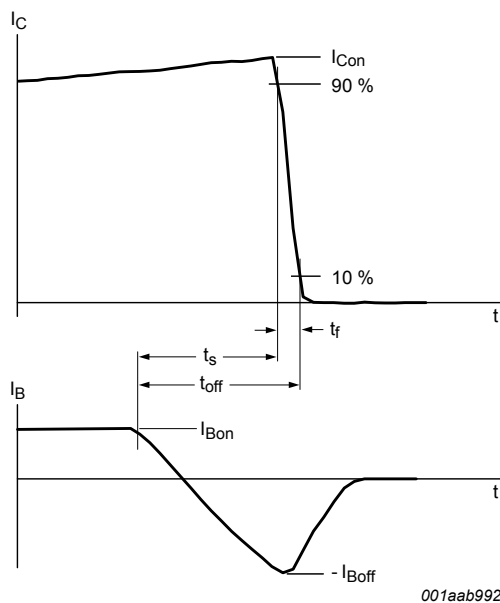


Fig. 15. Switching times waveforms for inductive load

10. Package outline

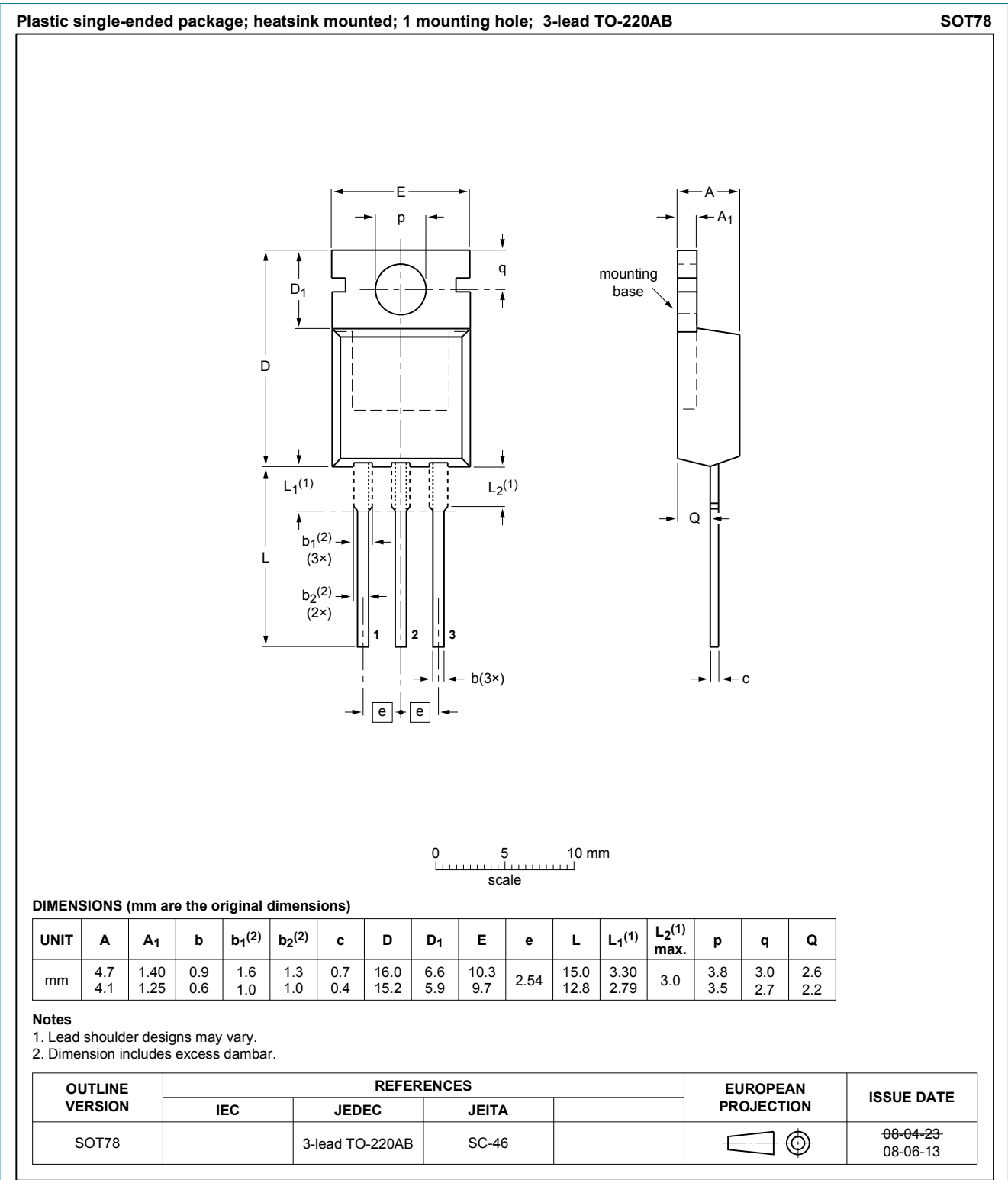


Fig. 16. Package outline TO-220AB (SOT78)

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Date of release: 21 January 2014